

IN THE SPECIFICATION:

Please amend the first full paragraph appearing on page 2 as follows:

~~Cross-Reference~~ Cross-Reference to Related Application: This application is a divisional of application Serial No. 09/028,134, filed February 23, 1998, ~~pending~~, now U.S. Patent 6,314,639, issued November 13, 2001.

Please amend the second full paragraph appearing on page 2 as follows:

Field of the Invention: This invention relates generally to semiconductor device assemblies. More particularly, the invention pertains to a method for producing a ~~chip-on-board~~ chip-on-board semiconductor device assembly with a heat spreading/dissipating member, and the device produced thereby.

Please amend the third full paragraph appearing on page 2 as follows:

State of the Art: In the design and production of modern integrated circuits (IC), an important consideration is the dissipation of heat generated in the semiconductor device. Elevated temperatures may cause irreparable damage to the semiconductor die and its electrical connections.

Please amend the sixth full paragraph appearing on page 2 as follows:

For higher power packaged devices, a metal heat spreader may be incorporated into the package or attached to the outside of the package. Because of the generally low thermal conductivity of polymers, the heat dissipation design is more critical for ~~polymer-packaged~~ polymer-packaged devices than for those packaged in ceramic or metal.

Please amend the paragraph bridging pages 2 and 3 as follows:

~~The use of heat~~ Heat spreaders/heat sinks/heat dissipaters in packaged semiconductor devices are often used to conduct heat to the exterior of the devices, either directly or via the leads. A wide variety of such is illustrated in United States Patent 5,596,231 of Combs, United States Patent 5,594,282 of Otsuki, United States Patent 5,598,034 of Wakefield, United States

Patent 5,489,801 to Blish II, United States Patent 4,024,570 of Hartmann et al., United States Patents 5,378,924 and 5,387,554 of Liang, United States Patent 5,379,187 of Lee et al., United States Patent 4,507,675 of Fujii et al., United States Patent 4,642,671 of Rohsler et al., United States Patent 4,931,852 of Brown et al., United States Patent 5,173,764 of Higgins III, United States Patent 5,379,186 to Gold et al., United States Patent 5,434,105 to Liou, and United States Patent 5,488,254 to Nishimura et al.

Please amend the third full paragraph appearing on page 3 as follows:

The present invention comprises a high density semiconductor device assembly for electrical connection without wires to a substrate such as a circuit board. In a preferred embodiment, the invention comprises a chip-on-board (COB) device with a heat spreader/dissipater on its back side. The active surface on its "front side" may be attached in a bare die state to the substrate by lead bond methods known in the art, preferably by ball-grid-array (BGA) methods which simultaneously complete each of the conductive bonds between the semiconductor die and the circuit board.

Please amend the fourth full paragraph appearing on page 3 as follows:

The present invention also encompasses a "paddle frame" strip for (a) providing a heat spreader/dissipater on each semiconductor die, (b) supporting the semiconductor dice for die testing and/or (c) supporting the semiconductor dice for applying conductive bumps to the bond pads. The paddle frame strip may incorporate any number of paddle frames, and preferably has at least eight paddle frames.

Please amend the fifth full paragraph appearing on page 3 as follows:

The present invention further comprises a method for producing the high density semiconductor device with the heat ~~spreader/ dissipater.~~ spreader/dissipater.

Please amend the third full paragraph appearing on page 4 as follows:

FIG. 1 is a plan view of a portion of a paddle frame and attached semiconductor ~~dies~~ dice of the heat spreading chip scale package of the invention;

Please amend the paragraph inserted by amendment dated April 28, 2006, between the third and fourth full paragraphs on page 4 as follows:

~~Fig.~~ FIG. 1A is a plan view of a portion of a paddle frame and attached semiconductor ~~dies~~ dice of the heat spreading chip scale package of the invention;

Please amend the fourth full paragraph appearing on page 4 as follows:

FIG. 2 is a cross-sectional side view of a semiconductor die bonded to a paddle frame in accordance with the heat spreading chip scale package of the invention, as taken along line 2-2 of FIG. 1;

Please amend the sixth full paragraph appearing on page 4 as follows:

FIG. 4 is a side view of a circuit board upon which are reversibly mounted ~~paddle-bonded~~ paddle-bonded semiconductor ~~dies~~ dice with ball grid arrays in accordance with the heat spreading chip scale package of the invention; and

Please amend the seventh full paragraph appearing on page 4 as follows:

FIG. 5 is a cross-sectional side view of a circuit board upon which are reversibly mounted and resin-packaged, paddle-bonded semiconductor ~~dies~~ dice with ball grid arrays, in accordance with the heat-spreading chip scale package of the invention.

Please amend the paragraph bridging pages 4 and 5 as follows:

An improved high density semiconductor device assembly is provided by the present invention which is configured to be electrically attached to a ~~substrate~~ substrate, such as a circuit ~~board~~ board, by array bonding. A series of bare semiconductor devices of the invention may be mounted on a substrate in a closely packed arrangement. The semiconductor device is provided

with a heat sink/spreading/dissipating member. Following mounting on a substrate, the device or plurality of devices may be “packaged” with a protective polymeric sealer.

Please amend the second full paragraph appearing on page 5 as follows:

With reference to the drawings of FIGS. ~~1~~ 1, 1A, and 2, a metal strip 10 of heat conductive material is configured with multiple paddle frames 12. The metal strip 10 has left and right side rails 14, 16 and a series of sprocket holes 18 in the side rails for precise positioning of processing equipment and a plurality of semiconductor dice 20 which are attached to the metal strip. Each paddle frame 12 includes the side rails 14, 16, cross-members 26, and a generally centrally positioned metal paddle 22 which is attached to the side rails 14, 16 by paddle support bars 24 and to cross-members 26 by paddle support bars 28. A semiconductor die ~~20-20,~~ 20, having a first major surface 36 and an opposing second major surface ~~38-38,~~ 38, has second major surface 38 attached to a metal paddle 22 by semiconductor die attach- attachment methods known in the art. Exemplary of such semiconductor die attachment methods is attachment using a semiconductor die attach layer 30 of electrically non-conductive polymeric adhesive such as epoxy or polyimide. Alternatively, a semiconductor die attach layer 30 may be electrically conductive. As known in the art, a metal filled polymer, an unfilled conductive polymer such as a silver filled epoxy or polyimide, or a conductive gold-silicon eutectic material may be used. Thus, the semiconductor die attach layer 30 may be electrically conductive or insulative, depending upon the circuit configuration of the second major semiconductor die surface 38. Thus, for example, the second major surface 38 may be designed to be grounded to a ground plane surface, which may be the metal paddle 22.

Please amend the third full paragraph appearing on page 5 as follows:

The metal paddle 22 acts as a heat spreader/dissipater in the final semiconductor device assembly 40. Thus, while the semiconductor die attach layer 30 may be either electrically conductive or insulative, it preferably has an enhanced heat conductivity. Where the metal paddle 22 comprises a metal layer attached to a polymer layer, the semiconductor die attach layer 30 is attached to the metal surface 48 to enhance heat transfer (see drawing FIG. 3).

Please amend the first full paragraph appearing on page 6 as follows:

Each metal strip 10 with paddle frames 12 may be formed in the same manner as are lead frames in the art. The number of paddle frames 12 which may be incorporated into the metal strip 10 is limited only by the capability of a manufacturer's machines for semiconductor die attachment and die excising.

Please amend the second full paragraph appearing on page 6 as follows:

The paddle frame 12 includes the left and right side rails 14, 16 which are joined by ~~cross members~~ cross-members 26. The generally centrally located metal paddle 22 is supported from the left and right side rails 14, 16 and ~~cross members~~ cross-members 26 by paddle support bars 24, 28. Generally, no leads for electrical conduction are provided, although one or more of the paddle support bars 24, 28 may be used as leads in certain specific instances as shown in FIG. 1. No narrow "leads" common in lead frames are required in the paddle frame 12, resulting in greater ease of manufacture and increased reliability (see FIG. 1A).

Please amend the third full paragraph appearing on page 6 as follows:

The paddle frame 12 may be formed of a thin film of metal such as aluminum, silver, copper, or Alloy "~~42~~". "42." Typically, the metal paddle 22 is sized to completely cover the second major surface 38 of the semiconductor die 20 and preferably be somewhat larger. The thickness 44 of the metal paddle 22 is a function of the quantity of generated thermal energy, the semiconductor die size, the thermal conductivity of the semiconductor die attach material, and whether a packaging material overlies the metal paddle 22 in the final product. For generally low rates of heat generation, the paddle thickness 44 may be the minimum required by structural considerations. However, where the heat generation rate is very high, it may be necessary to increase the paddle thickness 44 to provide an increased heat sink capacity.

Please amend the fourth full paragraph appearing on page 6 as follows:

In many cases, the thickness 44 of the metal paddle 22 need only be sufficient to support the semiconductor die 20 prior to excision, and for uniform adherence to the semiconductor die 20. The paddle thickness 44 may typically range from about 0.5  $\mu\text{m}$  to about 5  $\mu\text{m}$ , but may vary from this range, particularly upwardly for enhancing heat sink capability. This range of paddle thickness 44 includes the typical thicknesses of lead frames of the prior art. Paddle frames 12 may be formed and joined to semiconductor dice 20 by tape automated bonding (TAB).

Please amend the fifth full paragraph appearing on page 6 as follows:

To singulate each semiconductor device ~~40 assembly~~, assembly 40, the paddle support bars 24, 28 are excised close to the metal paddle 22 with excisions 50 (see drawing FIG. 3).

Please amend the first full paragraph appearing on page 7 as follows:

Illustrated in drawing ~~FIG. 1~~ FIGS. 1 and 1A is a plurality of semiconductor dice 20 with conductive bond pads 32 on the first major surface 36, ~~i.e.~~ i.e., the “active” surface. While ~~drawing FIG. 1 shows~~ FIGS. 1 and 1A show the conductive bond pads 32 along the periphery of the semiconductor dice 20, thus limiting the number of conductive bond pads, the invention may be used for semiconductor dice having a full grid array of conductive bond pads as shown in drawing FIGS. 2 and 3.

Please amend the second full paragraph appearing on page 7 as follows:

In a preferred embodiment, conductive projections 34 such as solder bumps or balls are formed on the conductive bond pads 32, the projections enabling “gang” bonding, ~~i.e. flip-chip~~ i.e., flip-chip bonding, of the semiconductor die bond pads to the conductive traces 46 of a substrate 42 such as a circuit board. This is illustrated in drawing FIGS. 4 and 5, which show a plurality of semiconductor ~~devices~~ device assemblies 40 flipped and bonded to circuit connections, ~~e.g.~~ e.g., conductive traces 46 (see drawing FIG. 5), of a substrate 42 comprising a circuit board. The internal circuitry within the substrate 42 is not shown, being irrelevant to

the invention. The semiconductor ~~devices~~ device assemblies 40 may be bonded to a substrate 42 in a high density pattern and, being “bare” semiconductor dice 20, take up minimal space. The bonding may be completed by standard “flip-chip” methods, including thermal and/or pressure processes.

Please amend the third full paragraph appearing on page 7 as follows:

Each semiconductor device assembly 40 has a heat sink/spreader/dissipater 52 which was formerly a metal paddle 22 of a metal paddle frame 12. The heat sink/spreader/dissipater 52 has a generally exposed surface 54 for dissipating heat generated in the semiconductor device assembly 40.

Please amend the fourth full paragraph appearing on page 7 as follows:

As depicted in drawing FIG. 5, a sealant material 56 may be applied to the periphery of a semiconductor device assembly 40 and the space 58 between the semiconductor device assembly 40 and the substrate 42. The sealant material 56 seals the semiconductor device assembly 40 to the substrate 42 and protects the semiconductor device assembly from moisture, etc. The spaces between adjacent ~~devices~~ semiconductor device assemblies 40 may be readily filled with sealant material 56. The space 58 may be filled, for example, by injecting sealant material 56 through holes, not shown, in the substrate 42. Preferably, surface 54 of the heat sink/spreader/dissipater 52 is largely left uncovered to provide high heat dissipation.

Please amend the fifth full paragraph appearing on page 7 as follows:

Any sealant material 56 useful in packaging semiconductor device assemblies may be used, ~~including e.g.~~ including, e.g., epoxy, polyimide, etc.

Please amend the first full paragraph appearing on page 8 as follows:

A method of producing the semiconductor device assembly 40 includes the steps of:

Please amend the second full paragraph appearing on page 8 as follows:

1. producing a plurality of semiconductor dice 20 with integrated circuits as a wafer, each semiconductor die 20 having a first major surface 36 defined as an active surface with an array of conductive bond pads 32, ~~i.e.~~ i.e., input/output (I/O) pads, and a second, opposite major surface 38;

Please amend the fourth full paragraph appearing on page 8 as follows:

3. providing a conductive “paddle frame” metal strip 10 with multiple paddle frames 12, each paddle frame having a heat conductive metal paddle 22 connected to left and right side rails 14, 16 and cross-members 26 of the paddle frame 12 by paddle support bars 24, 28;

Please amend the fifth full paragraph appearing on page 8 as follows:

4. bonding a semiconductor die 20 to each metal paddle 22 of the paddle frame metal strip 10 with a thin semiconductor die attach layer 30 of adhesive or adhesive tape ~~of e.g.~~ of, e.g., epoxy or polyimide. The adhesive semiconductor die attach layer 30 may be provided with enhanced heat conductive properties. Alternatively, the second major surface 38 of the semiconductor die 20 may be bonded to the metal paddle 22 eutectically by formation ~~of e.g. of~~ e.g., a gold-silicon eutectic semiconductor die attach layer 30 or other electrically conductive material such as a specially designed polyimide.

Please amend the sixth full paragraph appearing on page 8 as follows:

5. conductive projections 34, ~~i.e.~~ i.e., balls or bumps (stud bumps) for reflow may be formed on the I/O conductive bond pads 32 of the semiconductor dice 20 either prior to or following attachment of the semiconductor dice to the metal paddles 22;

Please amend the seventh full paragraph appearing on page 8 as follows:

6. the semiconductor dice 20 may be tested in sequence in strip form, ~~i.e.~~ i.e., while the metal paddles 22 with attached semiconductor dice are connected to the paddle frame metal



strip 10. A test head (not shown) is placed to make temporary electrical connection with the conductive bond pads 32 or ~~bumps~~ conductive projections 34 for the conduction of parametric and functional tests. The testing may include additional tests typical of "burn-in" testing;

Please amend the eighth full paragraph appearing on page 8 as follows:

7. the paddle support bars 24, 28 connecting the metal paddles 22 to the paddle frame 12 are excised to free each semiconductor device assembly 40;

Please amend the ninth full paragraph appearing on page 8 as follows:

The semiconductor ~~devices~~ device assemblies 40 so produced are configured for mounting in a ~~"flip-chip"~~ "flip-chip" configuration, ~~i.e.~~ i.e., face down on a substrate 42 such as a circuit board, ~~e.g.~~ e.g., by reflowing under heat and/or by pressure or other methods as known in the art.

Please amend the first full paragraph appearing on page 9 as follows:

The metal paddle 22 attached to the second major surface 38 of each semiconductor die 20 comprises a heat sink/spreader/dissipater 52 which prevents overheating of the semiconductor device assembly 40 (a) during testing (including burn-in), (b) during mounting on the substrate 42, (c) during packaging, and (d) in actual operation.

Please amend the second full paragraph appearing on page 9 as follows:

Following attachment to a substrate 42 such as a circuit board, the semiconductor device assembly 40 may be sealed with an electrically insulating sealant material 56 to produce a partially encapsulated package. The exposed surface 54 of the heat sink/spreader/dissipater 52 is preferably left largely uncovered, or is only thinly covered with the sealant material 56. The sealant may be any of the polymeric materials commonly used for packaging, including those used for ~~"glob-top"~~ "glob-top". Examples of such materials are epoxy resins and polyimides.

Please amend the third full paragraph appearing on page 9 as follows:

The invention is particularly applicable to high density integrated circuit semiconductor device assemblies 40 having a large number of interconnections, ~~i.e.~~ i.e., conductive bond pads 32. Such devices may produce significant quantities of thermal energy which, if not removed, may lead to destruction of the integrated circuit. The bare semiconductor dice 20 of the invention may be densely mounted on a substrate 42 and then sealed by introducing a sealant material 56 between the substrate and semiconductor dice to surround the electrical connections and the first major or active surfaces 36 and edges 60 of the semiconductor dice 20.

Please amend the fifth full paragraph appearing on page 9 as follows:

1. The ease of device handling is enhanced. The semiconductor dice 20 are fixed to the unseparated metal paddles 22 of the "paddle frame" 12 during the test process and each semiconductor device assembly 40 can be handled without touching the semiconductor die. Once the semiconductor device assembly 40 is separated from the paddle frame 12 by excision of the paddle support bars 24, 28, the metal paddle 22 becomes a heat sink/spreader/dissipater 52, and the device may be handled and supported solely thereby.

Please amend the sixth full paragraph appearing on page 9 as follows:

2. Current methods of lead frame production may be used to produce the paddle frame metal strip 10. The paddle frames 12 are much simpler in design than lead frames, there being few or no electrical leads.

Please amend the first full paragraph appearing on page 10 as follows:

3. Semiconductor dice or multiple chips 20 may be mounted on a single paddle frame metal strip 10, using equipment widely used by device manufacturers. Thus, reliable attachment of the semiconductor dice 20 to the metal paddles 22, testing (and burn-in) of the semiconductor dice, separation of the paddle mounted semiconductor dice from the paddle frame metal strip 10, and mounting of the semiconductor dice on a substrate 42 may be easily accomplished using well-developed and common assembly equipment and methods. The readily

aligned semiconductor die attach apparatus, test head, and lead excision apparatus enable accuracy and ease of operation in the device assembly.

Please amend the third full paragraph appearing on page 10 as follows:

5. Use of known technology and equipment results in a lower assembly cost. No additional ~~specialty designed~~ specialty designed equipment is required.

Please amend the fifth full paragraph appearing on page 10 as follows:

It is apparent to those skilled in the art that various changes and modifications may be made to the semiconductor die with the heat spreader/dissipater and the novel method of manufacturing, testing and installing the semiconductor die of the invention as disclosed herein without departing from the spirit and scope of the invention as defined in the following claims.